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## Silicon PNP Power Transistor

## 2SA1327

### DESCRIPTION

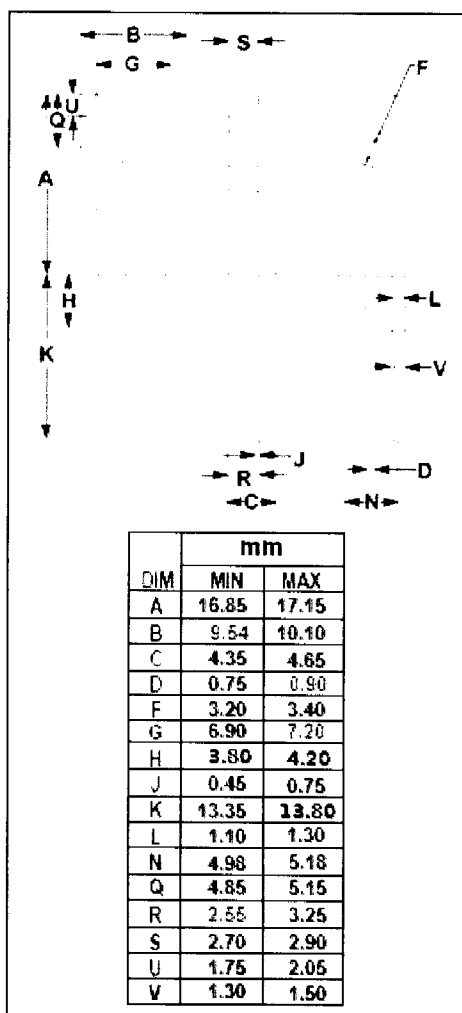
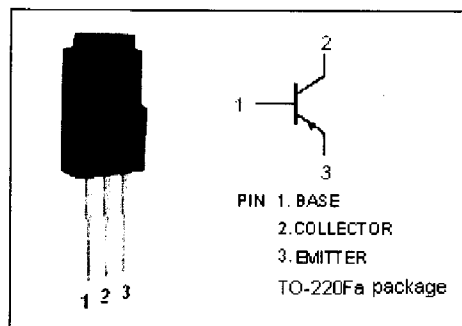
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -0.5V(\text{Max.}) @ I_C = -8A$
- High DC Current Gain-  
:  $h_{FE} = 70(\text{Min.}) @ I_C = -8A$

### APPLICATIONS

- Strobe flash applications.
- Audio power amplifier applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-20	V
$V_{EBO}$	Emitter-Base Voltage	-8	V
$I_C$	Collector Current-Continuous	-10	A
$I_{CM}$	Collector Current-Pulse	-20	A
$I_B$	Base Current-Continuous	-2	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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**Silicon PNP Power Transistor****2SA1327****ELECTRICAL CHARACTERISTICS** $T_j=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-20			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -8\text{A}; I_B = -0.4\text{A}$			-0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -8\text{A}; V_{CE} = -2\text{V}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -50\text{V}; I_E = 0$			-1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -8\text{V}; I_C = 0$			-1.0	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	100		320	
$h_{FE-2}$	DC Current Gain	$I_C = -8\text{A}; V_{CE} = -2\text{V}$	70			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -2\text{V}$		45		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		400		pF

◆  **$h_{FE-1}$  Classifications**

O	Y
100-200	160-320